

What is claimed is:

1. A semiconductor device comprising:

a substrate;

a first conductive layer formed on the substrate;

5 a second conductive layer formed on the substrate
at a predetermined distance from the first conductive
layer;

an insulation film formed on upper surfaces of the
first conductive layer and the second conductive layer
10 and having a plurality of first opening portions to expose
either the first conductive layer or the second conductive
layer and one or more second opening portions to expose
neither the first conductive layer nor the second
conductive layer; and

15 a third conductive layer formed on an upper surface
of the insulation film in such a manner to fill up the
first opening portions and the second opening portions
for making electrical connection between the first
conductive layer and the second conductive layer by way
20 of the first opening portions;

wherein the second opening portions are formed
between a pair of the first opening portions along the
third conductive layer.

25 2. The semiconductor device of claim 1, wherein the
second opening portions are formed at a predetermined
distance between the first opening portions.

3. The semiconductor device of claim 1, wherein the
30 third conductive layer is formed by a conductive material
containing copper.

4. A semiconductor device comprising:
a substrate;
a first conductive layer formed on the substrate;
5 a second conductive layer formed on the substrate
at a predetermined distance from the first conductive
layer;
an insulation film formed on upper surfaces of the
first conductive layer and the second conductive layer
10 and having a plurality of opening portions to expose one
end portion of the first conductive layer or of the second
conductive layer; and
a third conductive layer formed on an upper surface
of the insulation film in such a manner to fill up the
15 opening portions for making electrical connection
between the first conductive layer and the second
conductive layer;
wherein the third conductive layer has a
predetermined wiring length to maintain the connection
20 even if the length of the third conductive layer in a
direction of longer length changes due to thermal
expansion or contraction, and has the electrical
connection between the first conductive layer and the
second conductive layer at both ends of the third
25 conductive layer by way of the opening portions.

5. The semiconductor device of claim 4, wherein the
third conductive layer is formed by a conductive material
containing copper.

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6. The method of fabricating a semiconductor device,

comprising the steps of:

forming a first conductive layer on a substrate;

forming a second conductive layer on the substrate
at a predetermined distance from the first conductive
5 layer;

forming an insulation film on upper surfaces of
the first conductive layer and the second conductive
layer;

forming in the insulation film a plurality of first
10 opening portions to expose either the first conductive
layer or the second conductive layer and a plurality of
second opening portions to expose neither the first
conductive layer nor the second conductive layer; and

forming a third conductive layer on an upper surface
15 of the insulation film in such a manner to fill up the
first opening portions and the second opening portions
for making electrical connection between the first
conductive layer and the second conductive layer by way
of the opening portions;

20 wherein the second opening portions are formed
between a pair of the first opening portions along the
third conductive layer.

7. A method of fabricating a semiconductor device,
25 comprising the steps of:

forming a first conductive layer on a substrate;

forming a second conductive layer on the substrate
at a predetermined distance from the first conductive
layers;

30 forming an insulation film on upper surfaces of
the first conductive layers and the second conductive

layers;

forming in the insulation film a plurality of opening portions to expose either one end portion of the first conductive layer or of the second conductive layer;

5 and

forming a third conductive layer on an upper surface of the insulation film in such a manner to fill up the opening portions and to make electrical connection with the first conductive layer and the second conductive

10 layer;

wherein the third conductive layer has a predetermined wiring length to maintain the connection even if the length of the third conductive layers in a direction of longer length changes due to thermal expansion or contraction, and has the electrical connection between the first conductive layer and the second conductive layer at both ends of the third conductive layer by way of the opening portions.

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